

PNP EPITAXIAL SILICON TRANSISTOR

GENERAL PURPOSE APPLICATION

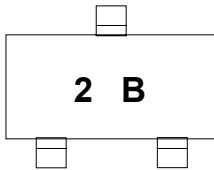
SWITCHING APPLICATION

- ◇ Collector Current $I_c=600\text{mA}$
- ◇ Complementary to WST2222/S

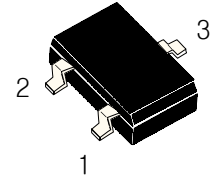
ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CB0}	-60	V
Collector-Emitter Voltage	V _{CEO}	-40	V
Emitter-Base voltage	V _{EBO}	-5	V
Collector Current	I _c	-600	mA
Collector Power Dissipation	P _c	TO-92 :.650 SOT-23(S):350	mW
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	-55~+150	°C

◇Mark Information

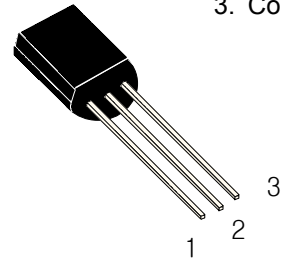


SOT-23



1. Emitter
2. Base
3. Collector

TO-92



◇Ordering Information

Device	Package
WST2907	TO-92
WST2907S	SOT-23

ELECTRICAL CHARACTERISTICS

(Ta=25°C, unless otherwise specified)

Characteristic	Symbol	Test Condition	Min	TYP	MAX	Unit
Collector-base breakdown voltage	BV _{CB0}	I _c =-10μA, I _E =0	-60			V
Collector-emitter breakdown voltage	BV _{CEO}	I _c =-10mA, I _B =0	-40			V
Emitter-base breakdown voltage	BV _{EBO}	I _E =-10μA, I _C =0	-5			V
Collector cut-off current	I _{CBO}	V _{CB} =-50V, I _E =0			-20	nA
DC current gain	h _{FE}	V _{CE} =-10V, I _c =-10mA	75			
Collector-emitter saturation voltage	V _{CE(sat)}	I _c =-150mA, I _B =-15mA I _c =-500mA, I _B =-50mA			-0.4 -1.6	V
Base-emitter saturation voltage	V _{BE(sat)}	I _c =-150mA, I _B =-15mA I _c =-500mA, I _B =-50mA			-1.3 -2.6	V
Output Capacitance	C _{ob}	V _{CB} =-10V, f=1MHZ			8	PF
Transition Frequency	f _T	V _{CE} =-20V, I _c =-50mA	250			MHZ
Turn on Time	t _{ON}	V _{cc} =-30V, I _c =-150mA, I _{B1} =-15mA			45	ns
Turn off Time	t _{OFF}	V _{cc} =-6V, I _c =-150mA, I _{B1} =I _{B2} =15mA			100	ns

